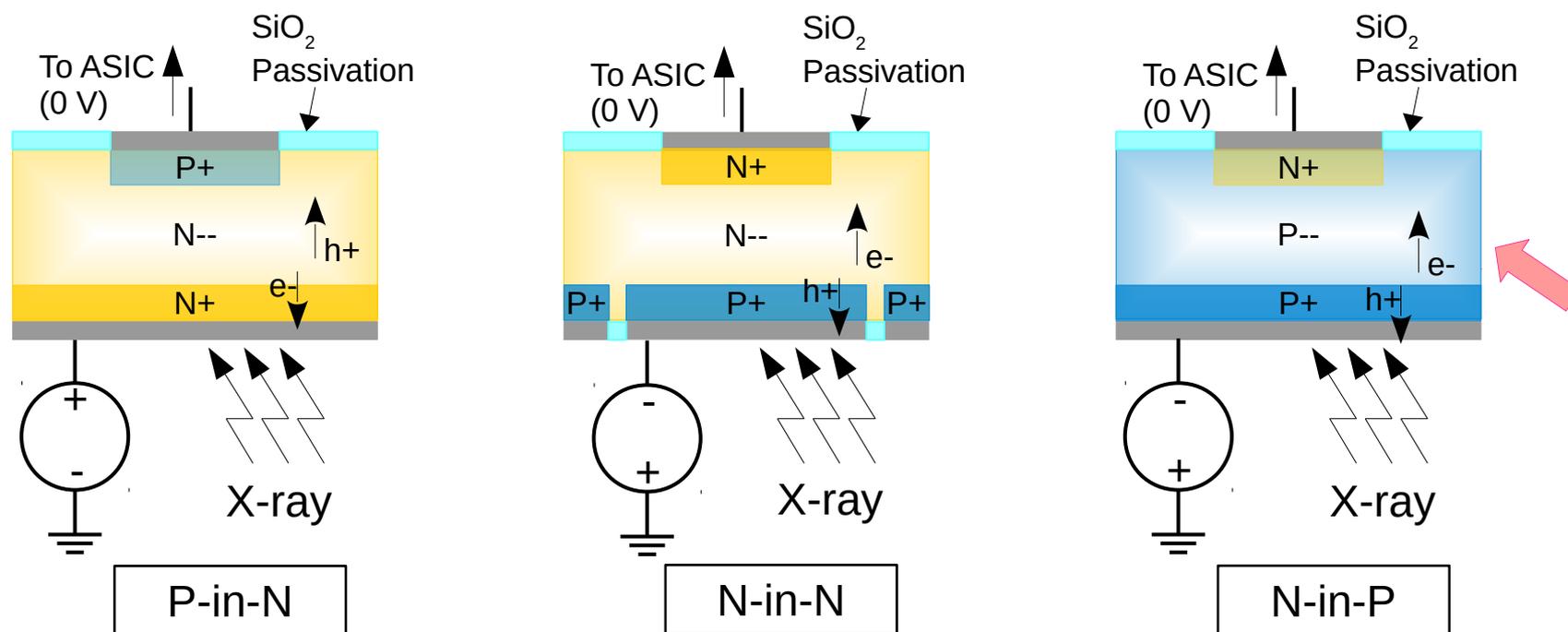


Guard Ring Optimization

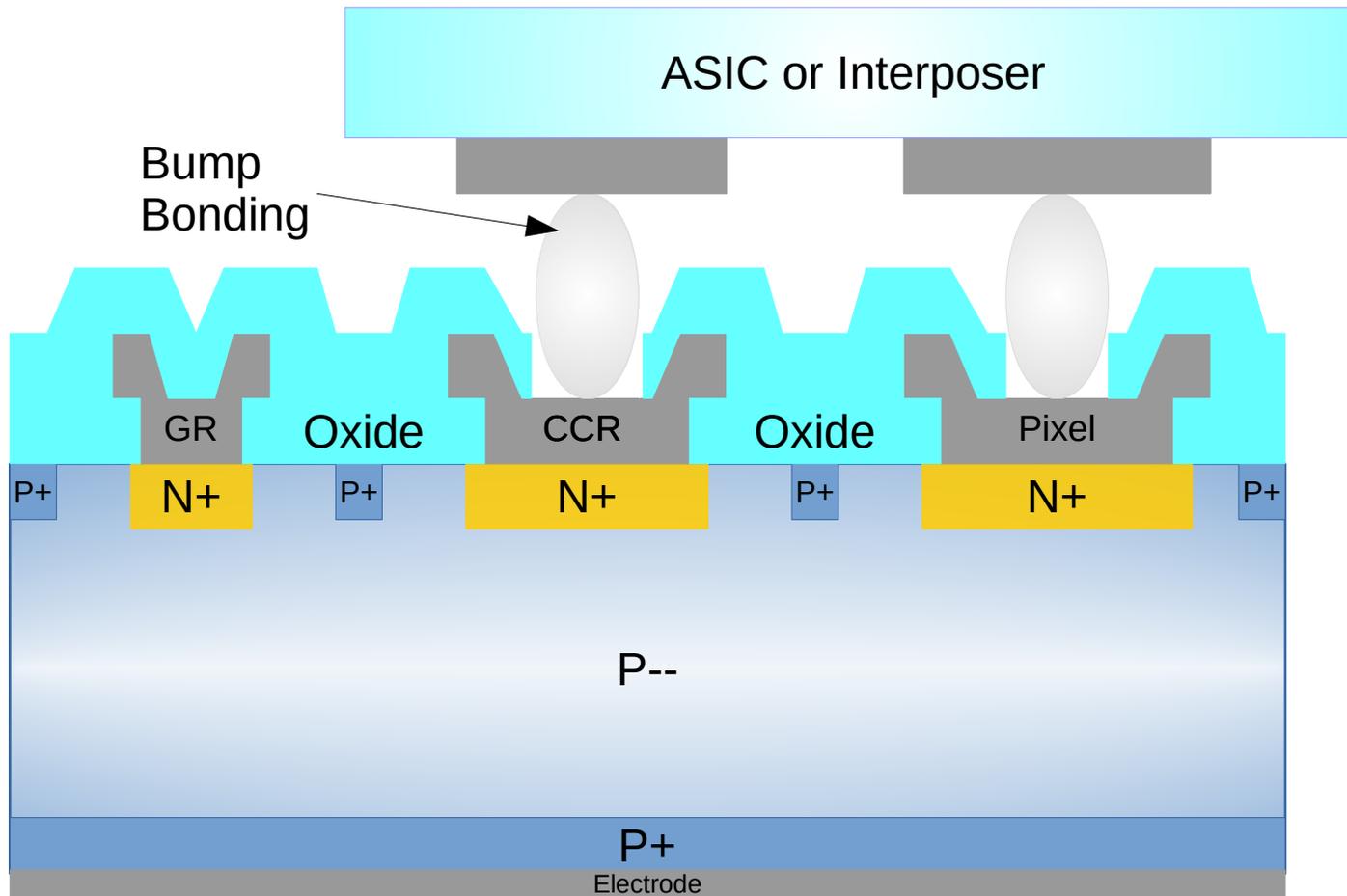
Taylor Shin
(January 20th 2016)

Silicon Diode Detectors

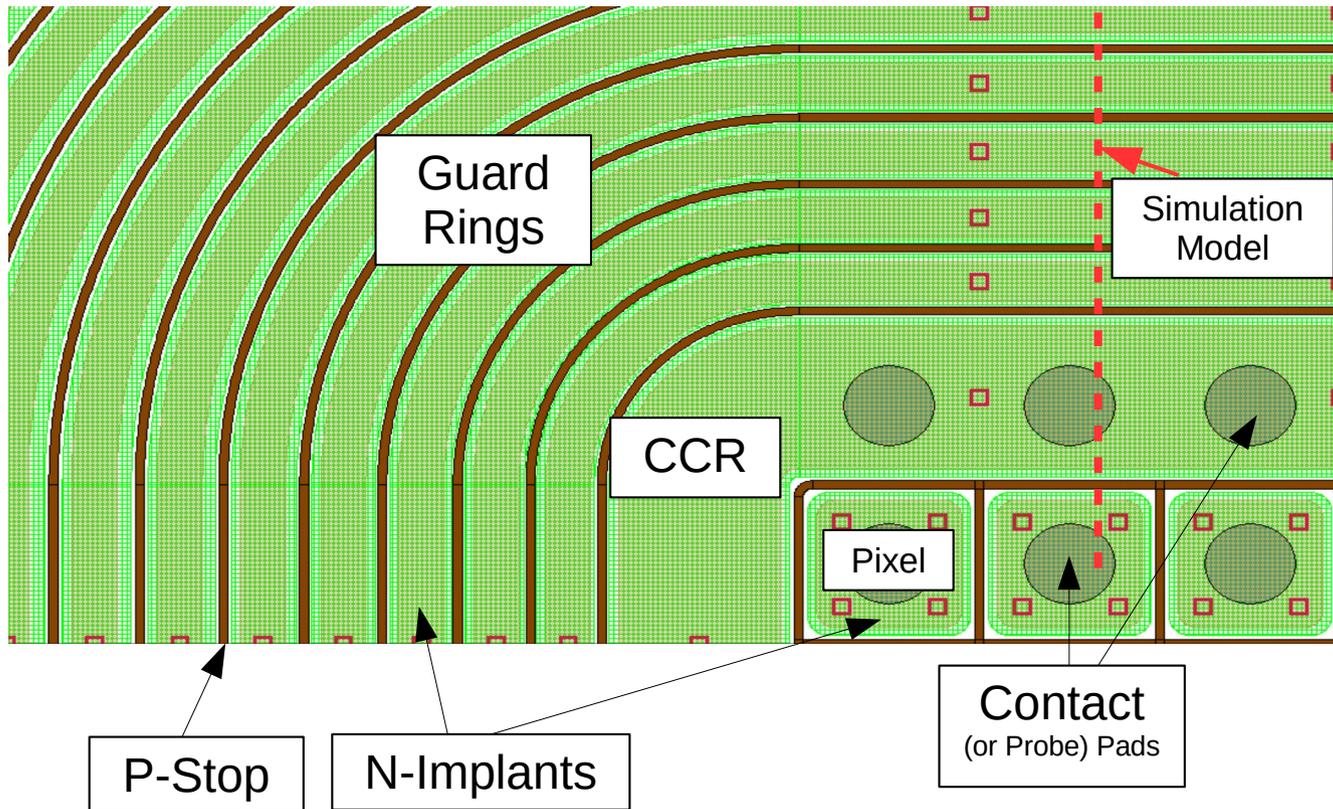


- **P-in-N**: Most widespread technology so far due to simplicity and affordable substrate from FZ process. However, uses rather slow holes as a main signal carrier and the substrate type changes after lots of high energy X-ray radiation.
- **N-in-N**: Faster than P-in-N since **electron** is a major signal carrier. But requires double side process to implement guard rings (The depletion region stretches from the back electrode rather than from pixels) but stronger than P-in-N in terms of radiation hardness. → Problem: So complex to manufacture. (note that process difficulty jumps with mask numbers, exponentially.)
- **N-in-P**: Fast. Also much stronger (in terms of radiation hardness) since the substrate is already P-type. The P-type substrate supply was problematic but not anymore.

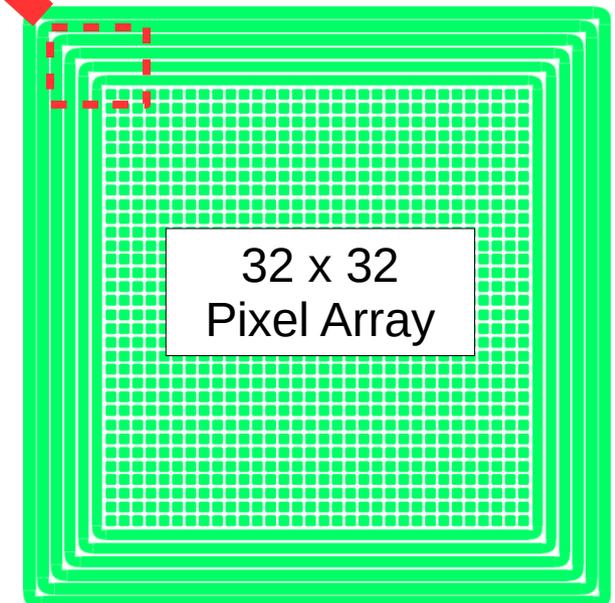
N-in-P Prototype Structure



Mask View of the FASPAX 15 GR Sample



Guard rings are not biased at all.
(Floating Guard Rings)



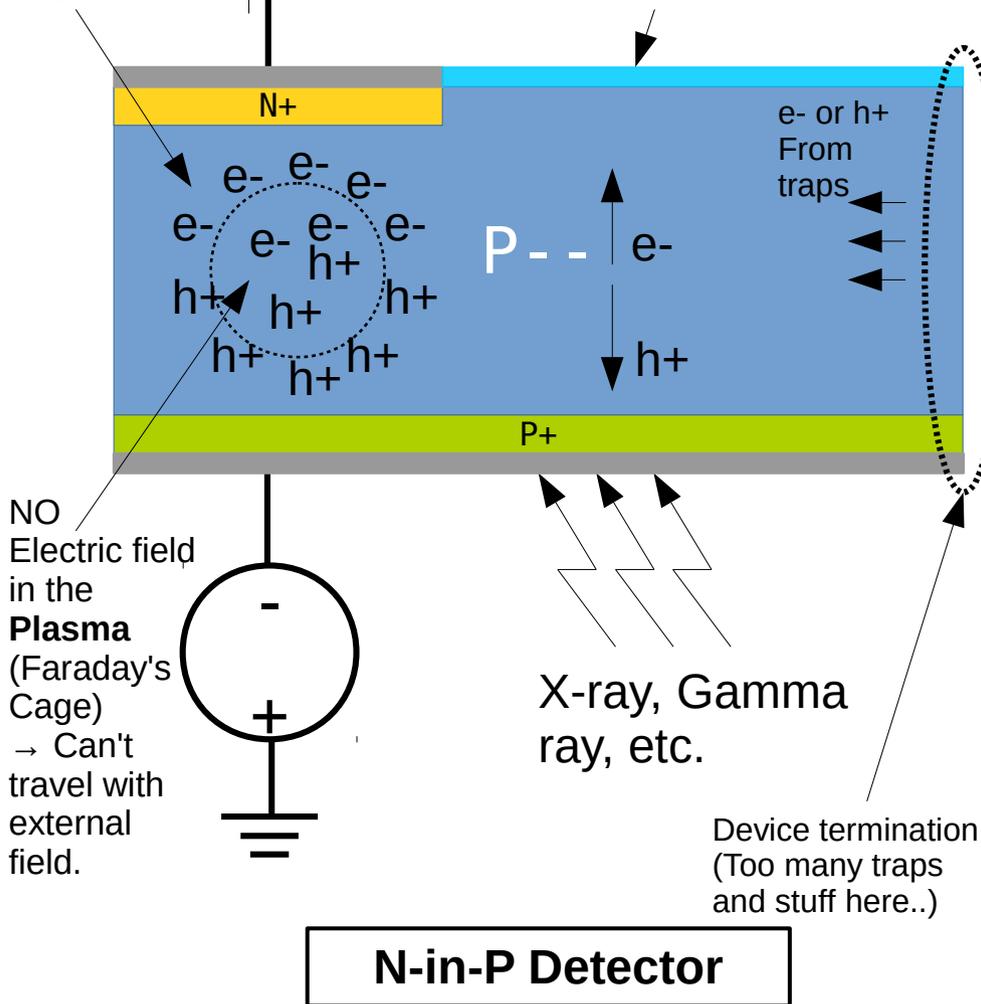
CCR is a biased (to ground) guard ring which collects additional leakage current.
(Current Collection Ring)

Problem – Plasma Delay Effect

So many Photo-generated carriers form a closed region

To Readout ASIC (0 V)

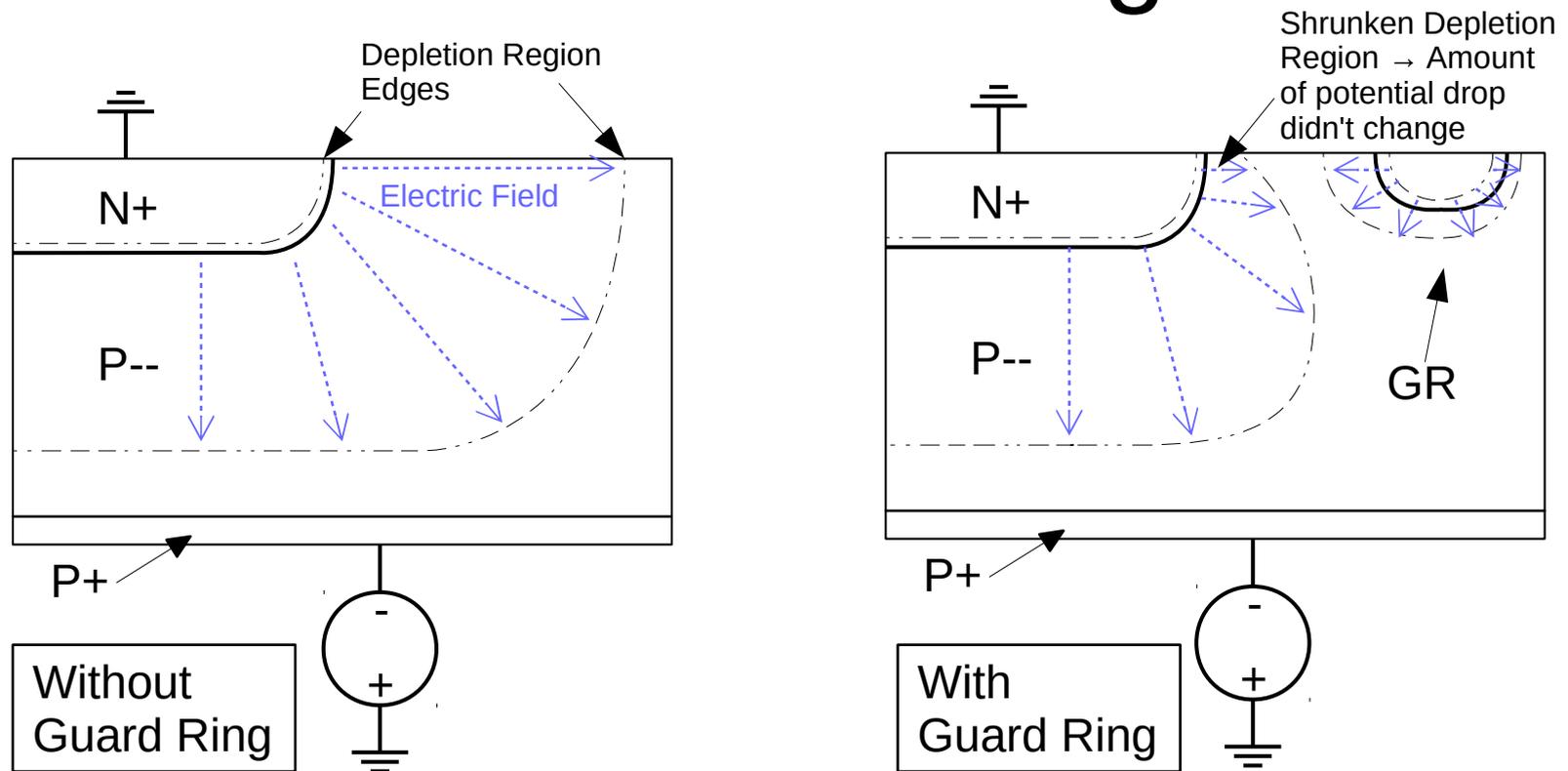
Oxide Passivation



N-in-P Detector

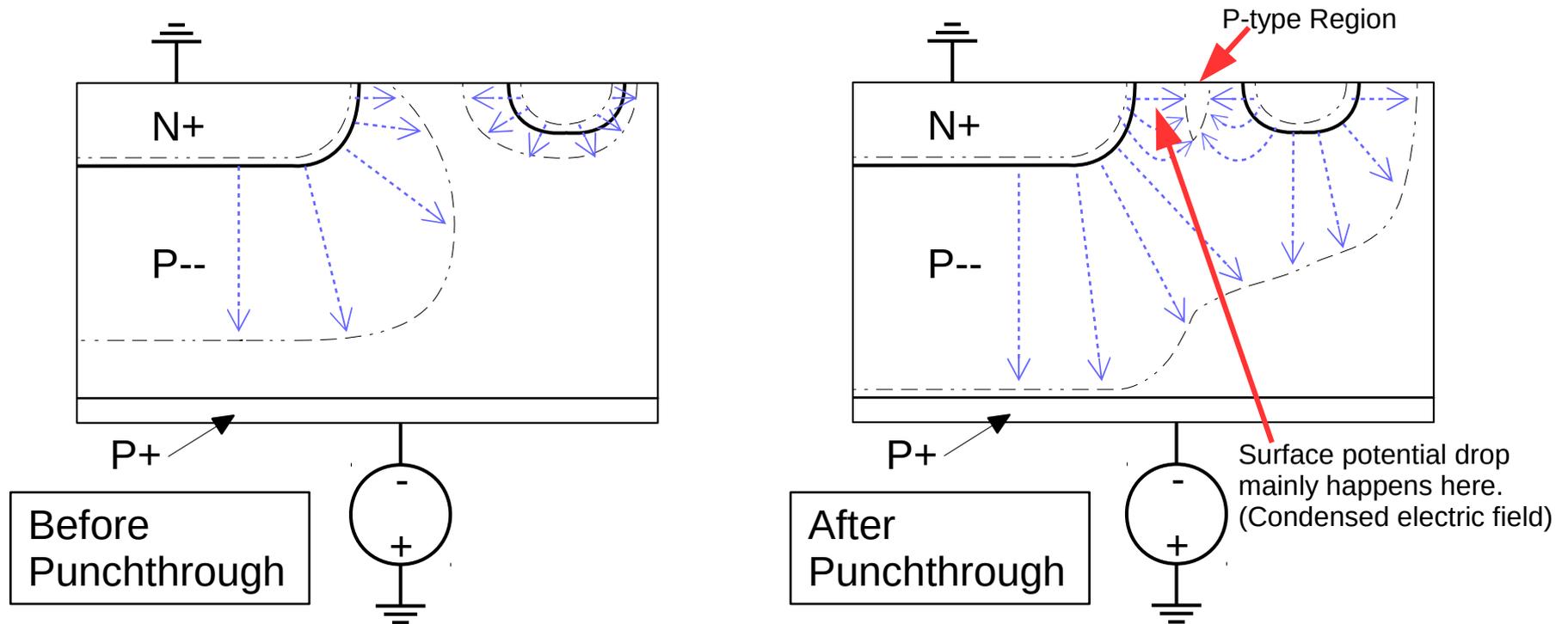
- Problem: the upgraded beamlines emit too many photons per bunch → causing Plasma Delay Effect
- To avoid such unexpected delay, we need to apply extremely high bias (~ 900 V?) across the silicon detector.
- Such high bias causes additional charge injection from device termination. → Additional noise
- Thus, we need to control potential drop at the detector surface (pixel side) in some way. → Guard rings from power electronics.

The Guard Rings



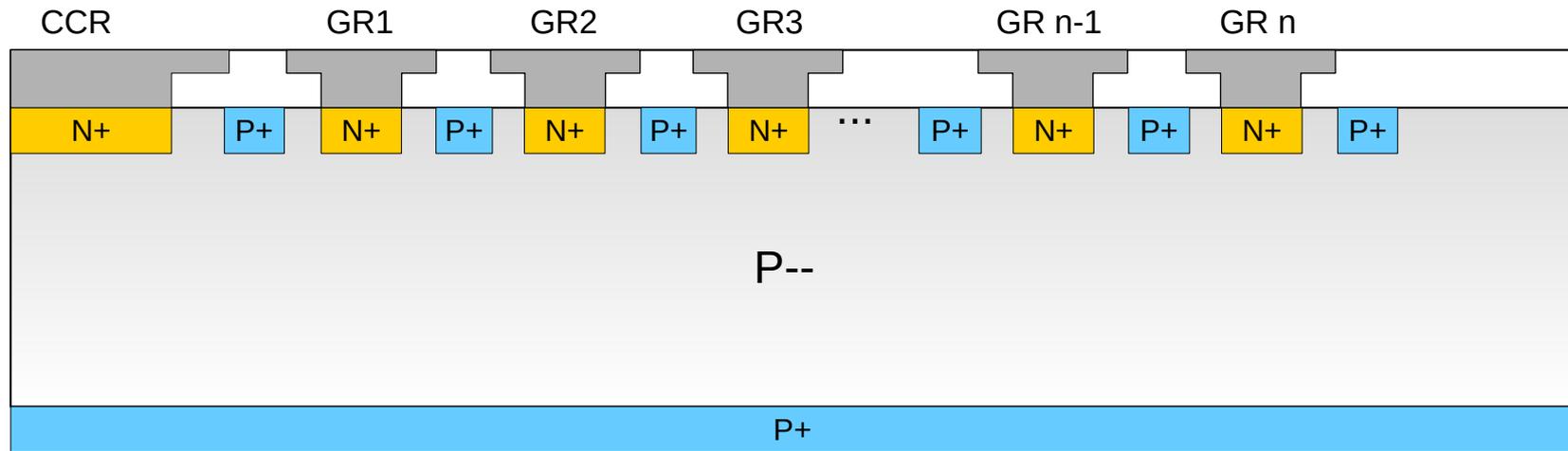
- Manipulates electric field to prevent it reaching the device termination.
 - When P-N was biased, depletion region extends from highly doped side. And the depletion region incorporates electric field. (Depletion region → Electric field.)
- Commonly used in power electronics.
- Currently, FASPAX project employs floating guard rings to simplify ASIC interface.
- The Guard ring (See right figure) disrupts the electric field advancement.

The Punchthrough



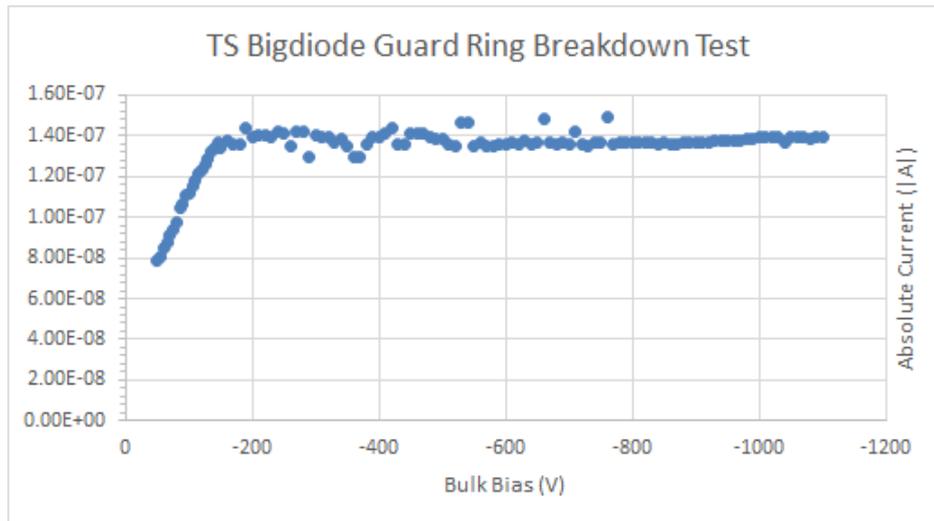
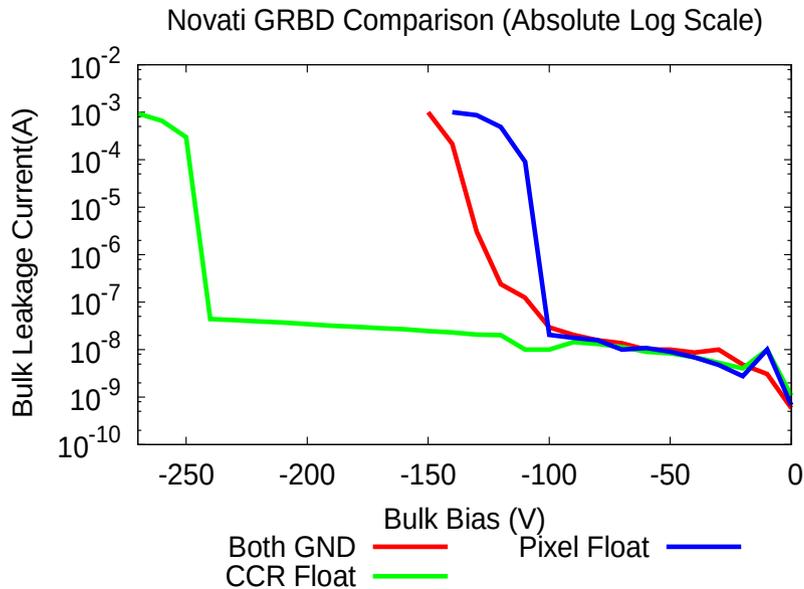
- In fact, we need too much bias to avoid the Plasma Delay Effect.
- If the bias is **too high**, a single guard ring is not enough. → The electric field from grounded contact overwhelms GR's counter electric field.
- In this case, we can't rely in N-type guard rings. → So we implemented a small p-type implants before the guard ring to condense the electric field strength even more.

FASPAX Guard Ring Structure (Simplified)



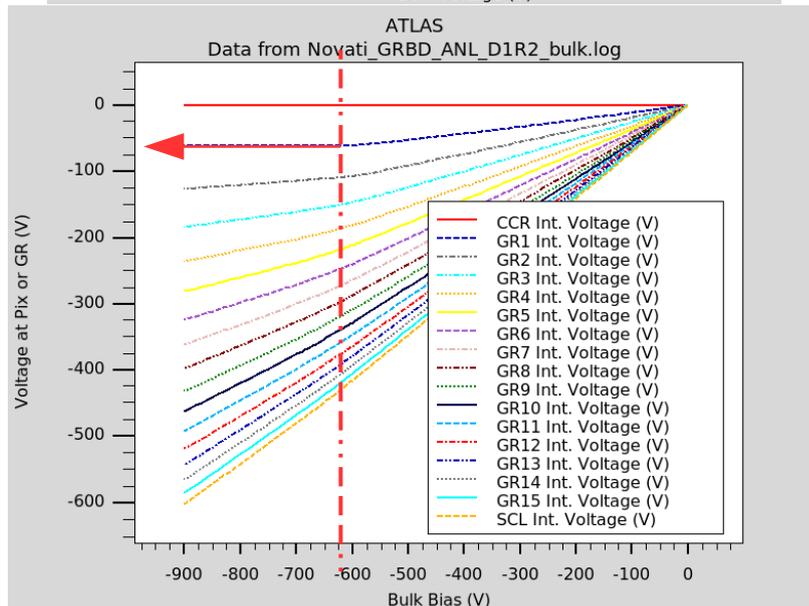
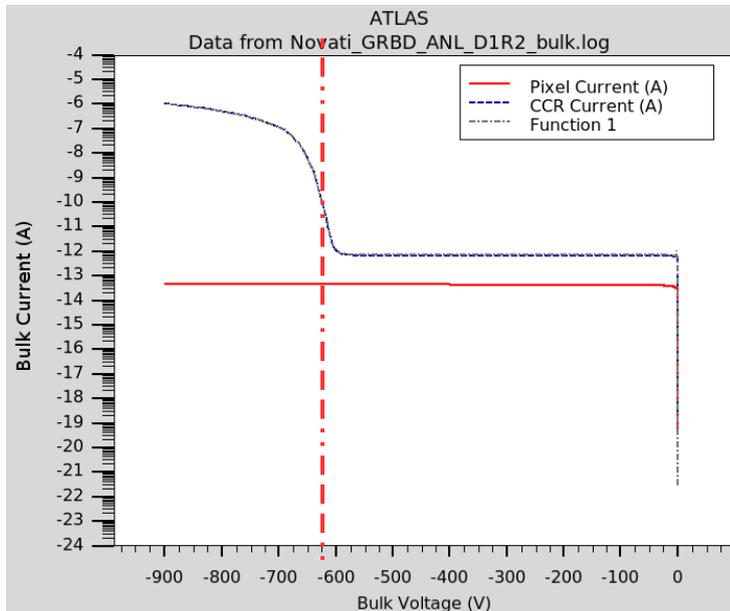
- Two variants: 8 guard rings or 15.
- Measurement has been performed on test samples has shown that the breakdown (~ -135 V of V bulk.) is actually happening earlier than expectation.
- We suspected the breakdown is actually happening somewhere at the guard ring surface.

I-V Sweep Results



- Upper Figure – FASPAX 15 GR p-stop sample.
 - Breaking down at (as low as) ~ -135 V of bias
 - CCR Float: CCR became a guard ring \rightarrow improved by twice but not enough.
 - We have taken the data from 16th row pixel.
- Lower Figure – FNAL Big Diode Device with 5 mm-wide, p-stop sample.
 - Two external biased guard ring design. (Similar to Hammamatsu photodiode they were working on.)
 - Also breaking down as low as -200 V.
 - The graph is kind of misleading with the leakage current of 0.1 μ A. But, in fact, we had some problem with compliance setting at the characterization system. (One reason why we ordered Keithley 4200.)
 - The voltage bias was actually limited to -185 V due to misleading (1/1000) compliance setting.

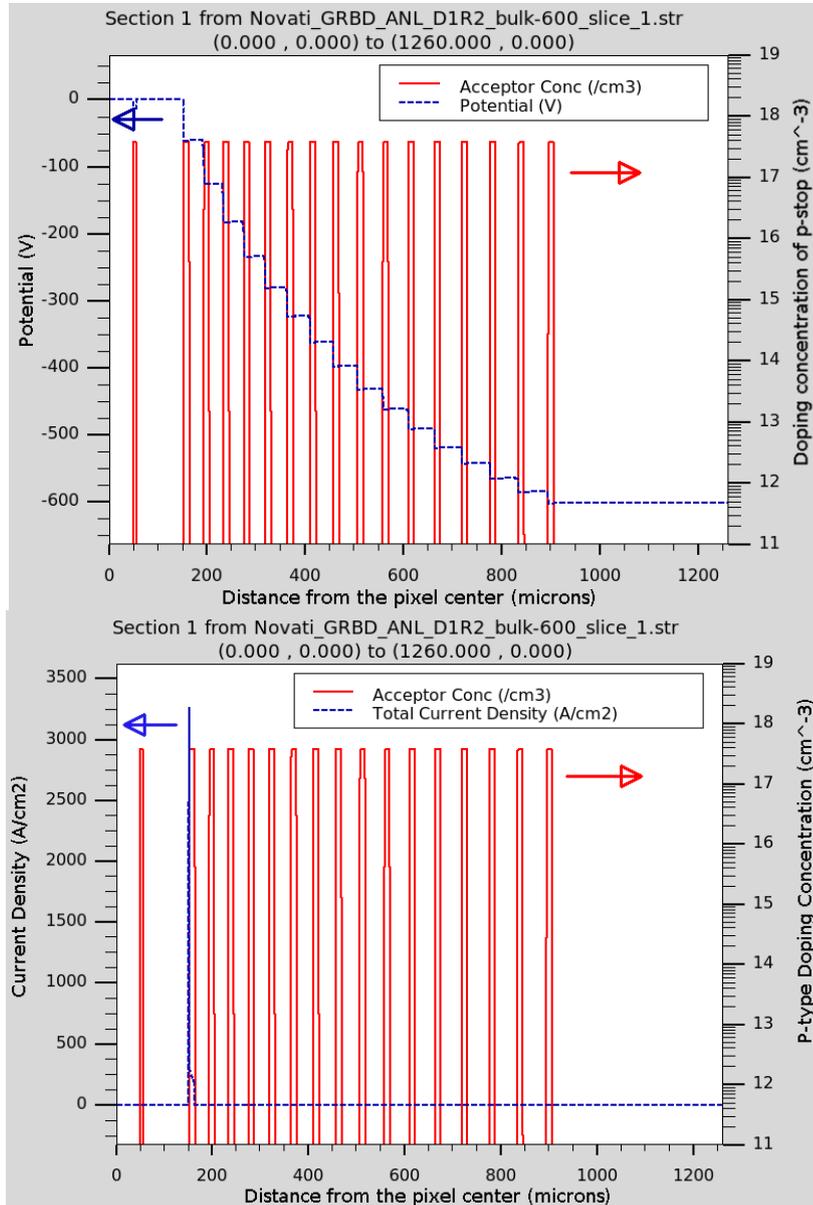
Simulation Result (I-V, Potential)



- Breakdown at -630 V.
 - Much higher than expected due to lack of trap state implementation in SiO_2 .
 - Also, the bulk silicon was assumed as intrinsic due to numerical issue.
 - This issue was resolved in recent batch of simulation model optimization with higher Q_{ss} of $6.7 \times 10^{12} / \text{cm}^2$
- Interface trap (Q_{ss}) was $8.8 \times 10^{11} / \text{cm}^2$. (sheet)
- The Potential of the first guard ring is at -63 V.
- The last floating guard ring potential is staying at -460 V when the bulk bias was -630 (breakdown point.)
 - 170 V bias across the detector at the termination.
 - Depletion region reached here. → Punchthrough control Failed.

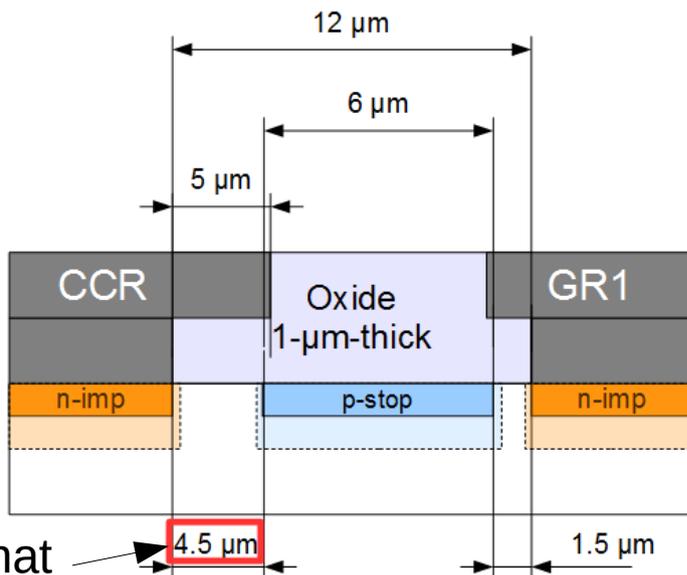
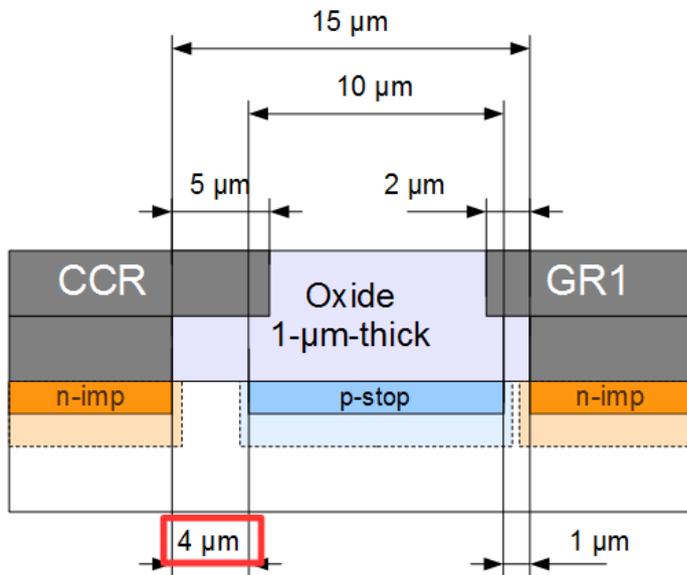
Simulated Breakdown

(Potential, Breakdown Current)



- **Blue line:** Potential and Current density
- **Red line:** Showing the location of p-stop implants.
- The potential drop per each guard ring decreases.
 - Optimal design can be achieved when all the potential drop equalizes.
- Obviously, **the first p-stop implant breaks down.**
 - Its vicinity is actually, N- i-P diode under reverse bias.

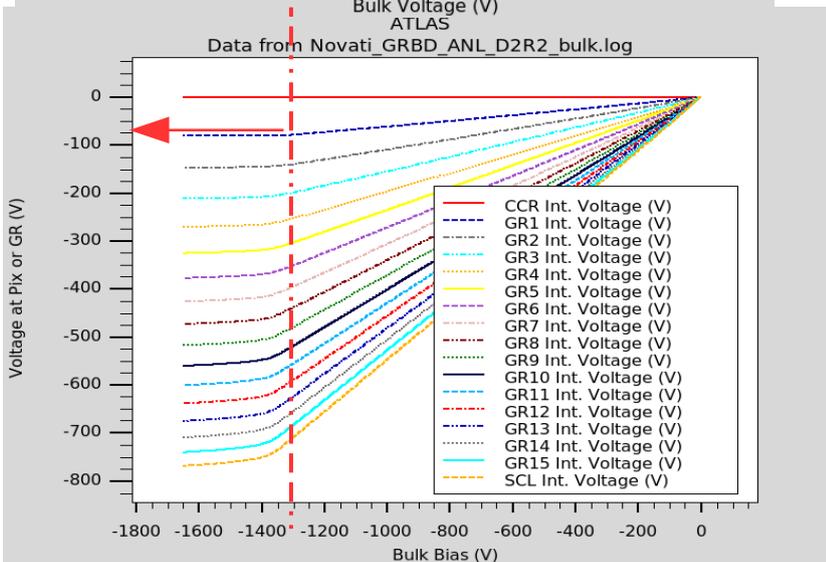
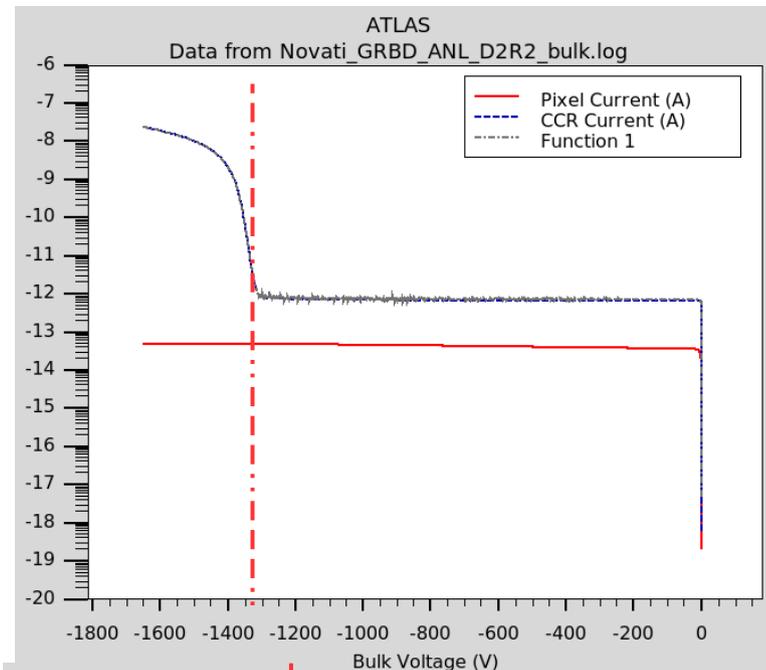
Shorter P-stop Width (10 μm \rightarrow 6 μm)



That gap...

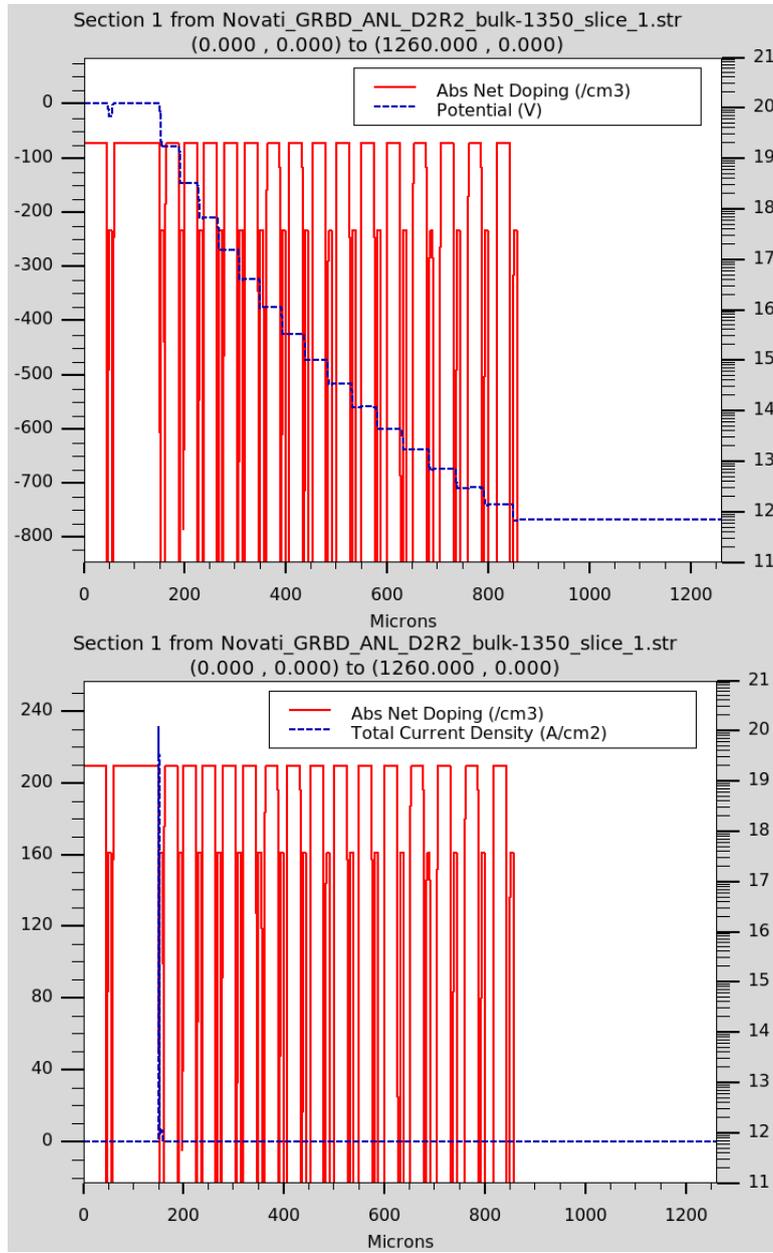
- One way or another, we need to fix the problem.
- Fundamentally, we can reduce doping concentration (either N+ or P-stop) but we don't have direct control on the process.
- Another alternative can be giving more distance from N+ contact to reduce electric field.
- By compromising the design constraints from wafer manufacturer, we reduced the 10- μm -wide p-stop implant to 6 μm . \rightarrow Obtained 0.5 μm more space.

2nd Design (I-V, Potential)



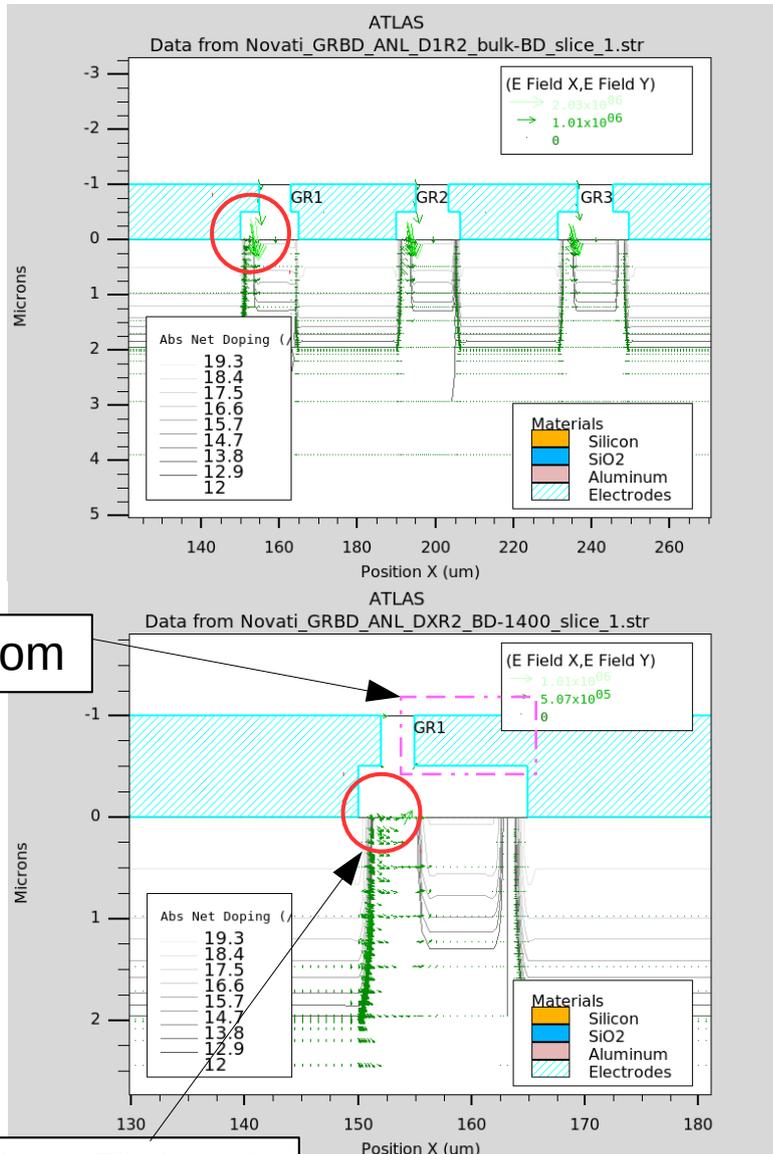
- The breakdown voltage jumped from 10 μm -gap design by twice.
- However, still failing at Punchthrough control.
 - Still, the simulation was obtained without proper bulk impurity.

2nd Design (Potential, Breakdown Current)



- Potential drop profile seems to be similar to previous 10 um design.
 - We would rather need to *spread* the GR implants.
- Again, the breakdown actually happened at the first guard ring.

3rd Design ('Shroom?')

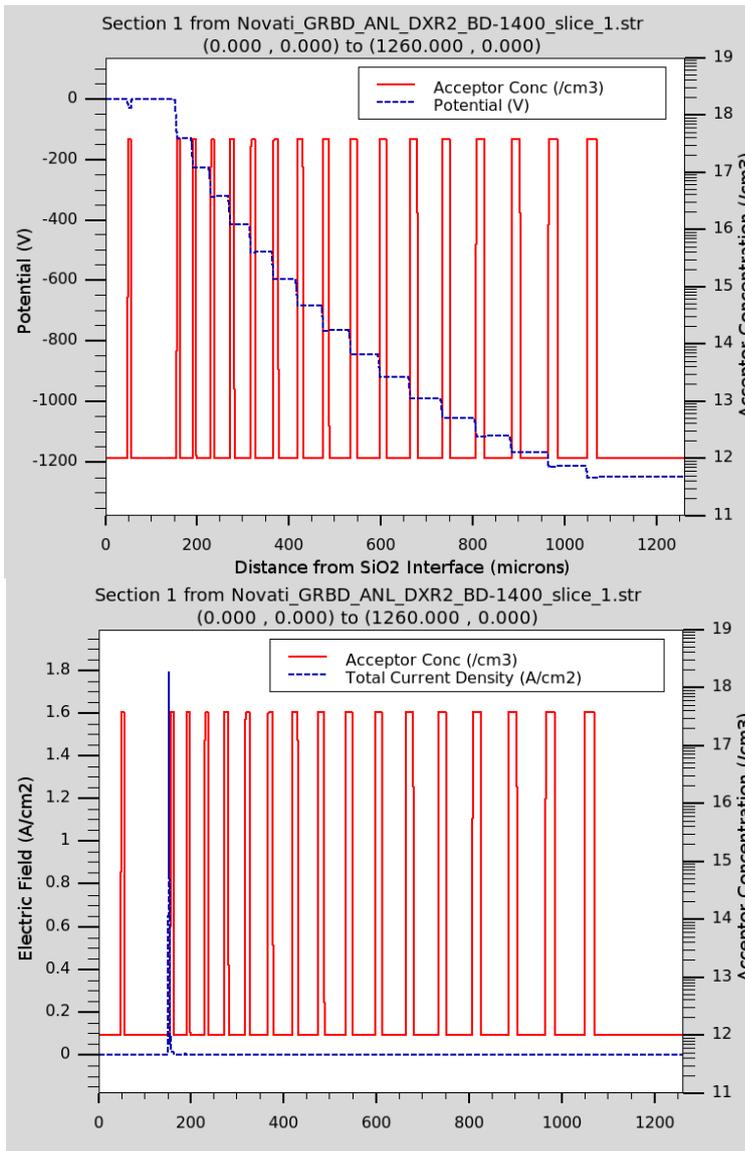


'Shroom

Almost Eliminated
Vertical Electric Field

- Sounds weird, but the overhang from previous (or left) electrode overlapping p-stop causes tons of electric field.
- Mainly, it is vertical direction and doesn't seem to be significant to the reverse biased N-i-P vicinity.
- However, [O. Koybasi, et al.](#) pointed out that the vertical electric field can be a menace.
- So, we decided to move the p-stop towards to next n+ implant and extended guard ring overhang → ('Shroom')
 - In fact, they point out that the 'Shroom doesn't need to be too long. So we stayed at 9 um-long to just cover the entire 6 um-wide p-stop implant.

3rd Design (Potential, Breakdown Current)

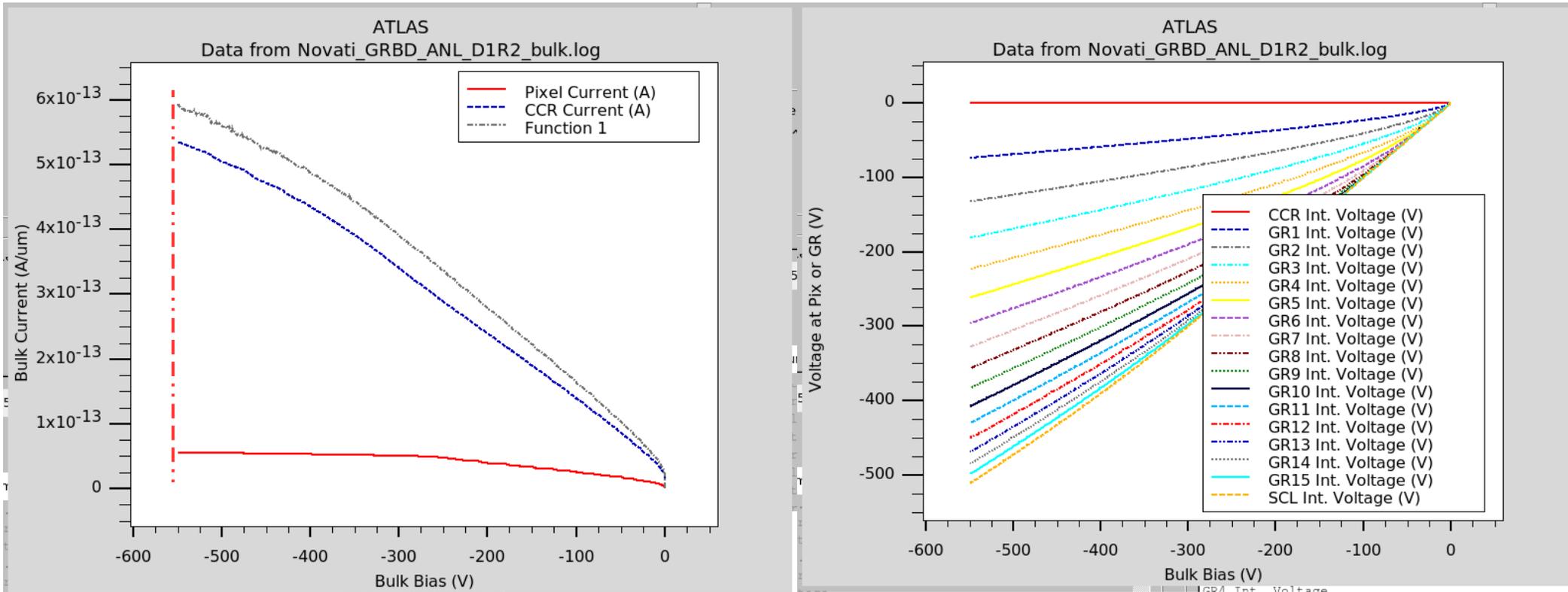


- Again, It breaks down at the first guard ring.
- The first guard ring sustains up to -120 V of bias which is technically doubled from previous design.
- The breakdown actually happened at -1250 V of bulk bias.
 - This time, the bulk is not intrinsic!! $1e12 \text{ cm}^{-3}$ of Boron
 - Such bulk implementation prev. device breakdown -750 V...
- Also, the last guard ring is as low as -1250 V → **controlled the Punch**
- So, I guess we nailed it!!



Comparison of three devices with
proper bulk impurity of $1e12 /\text{cm}^3$

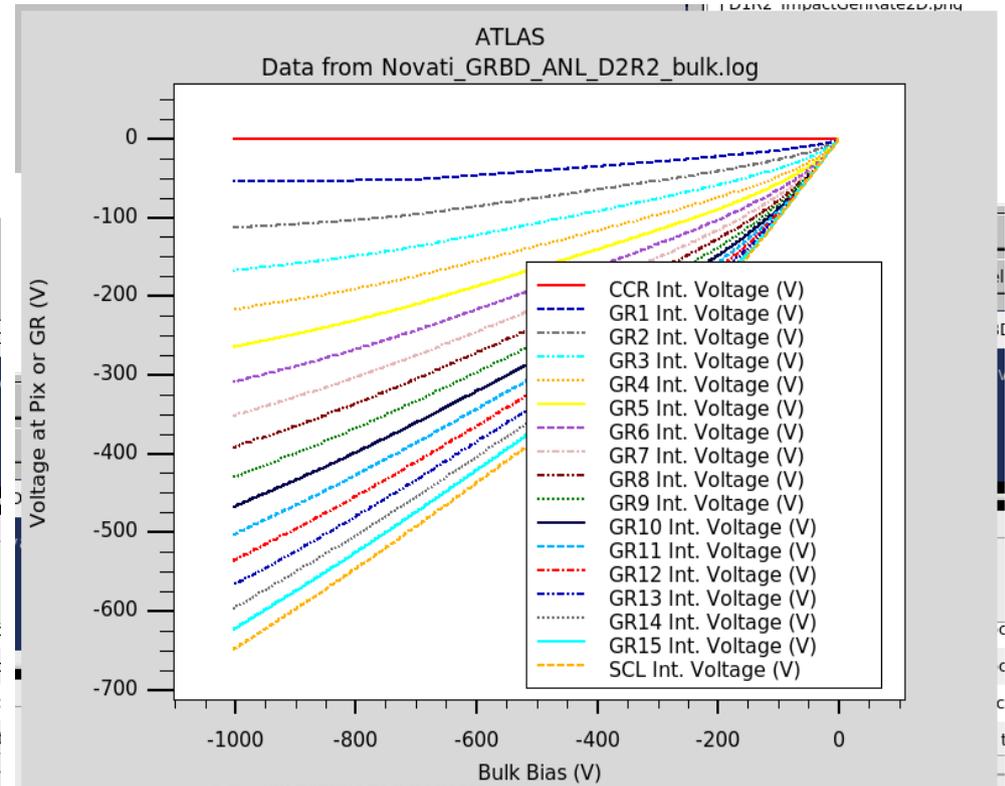
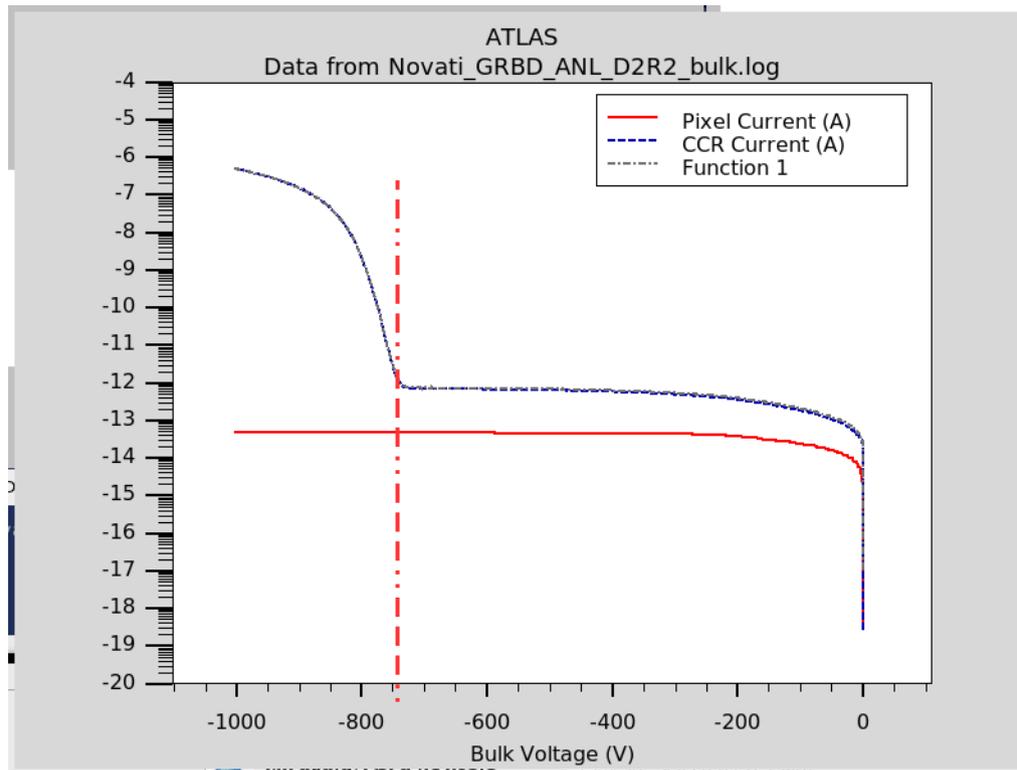
1st Device with Bulk Impurity ($1e12 \text{ cm}^{-3}$ Boron)



10-um-wide p-stop device:

Breakdown at -560 V? → Simulation convergence issue
Potential at the last GR: -510V → Punchthrough

2nd Device with Bulk Impurity ($1e12 \text{ cm}^{-3}$ Boron)

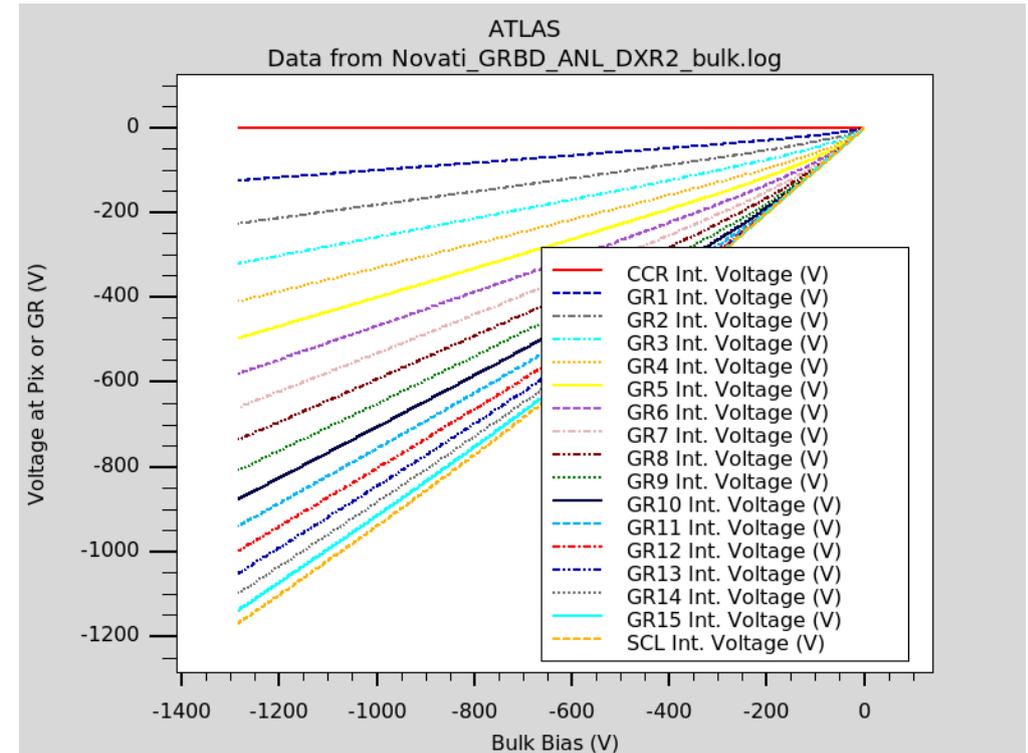
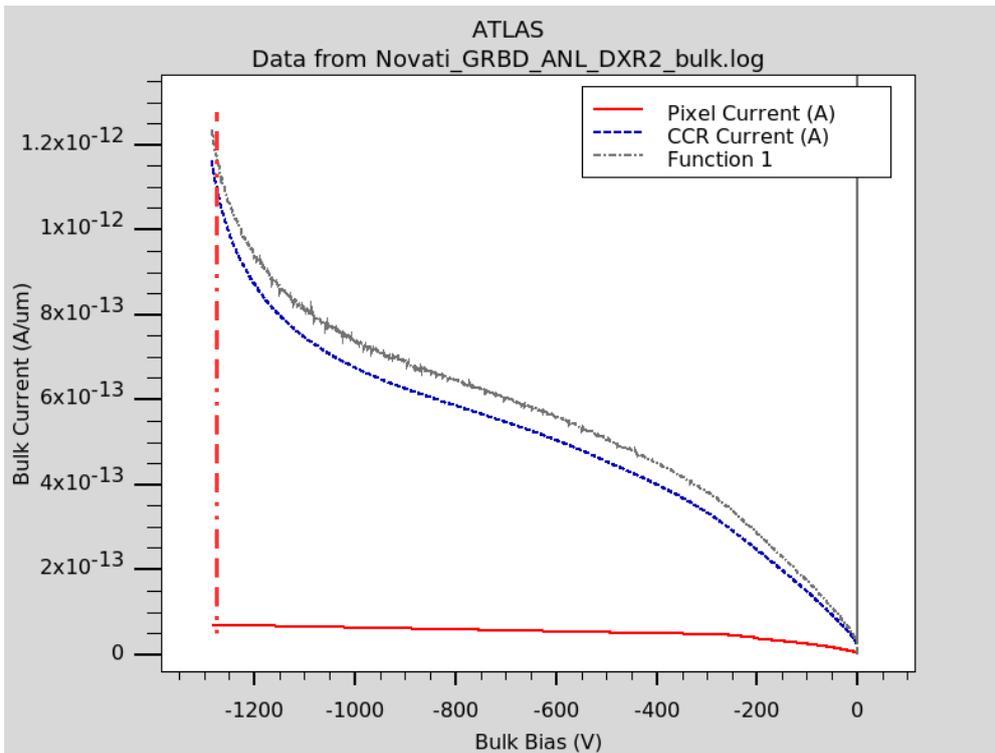


6 μm -wide p-stop device.

Breakdown at -750 V

Potential at the last GR: -550V \rightarrow Punchthrough

I-V Characteristic and potential from the 3rd device



'Shroom device

Breakdown at -1250 V

Potential at the last GR: -1250V → **NO** Punchthrough

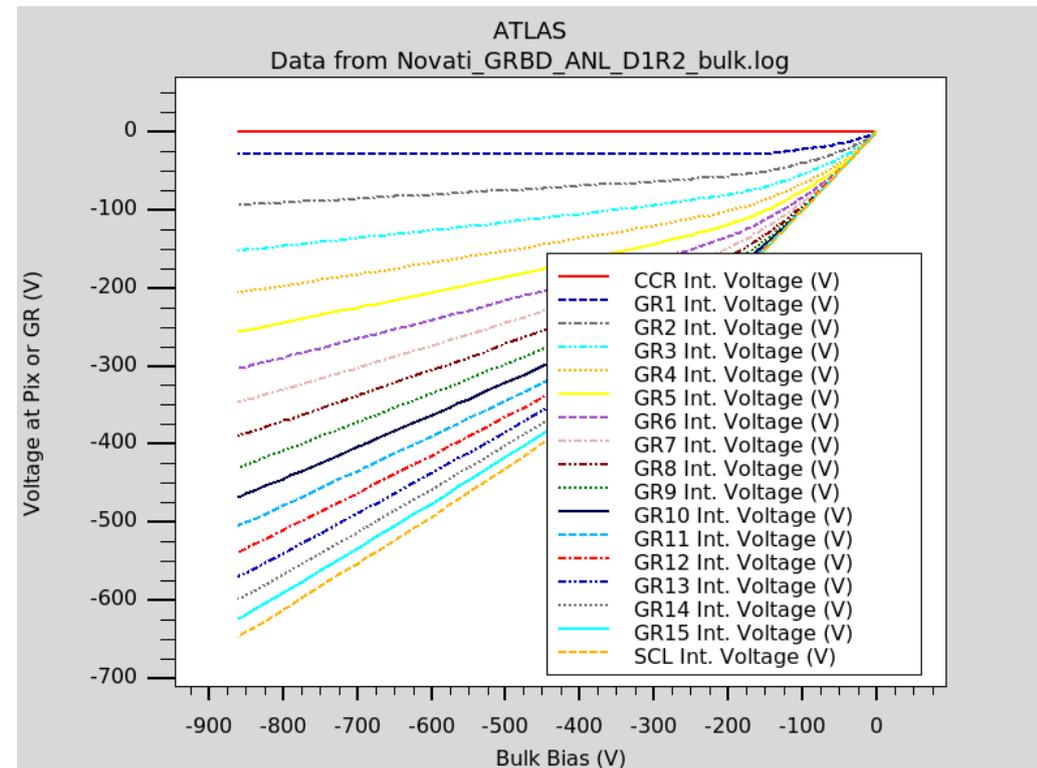
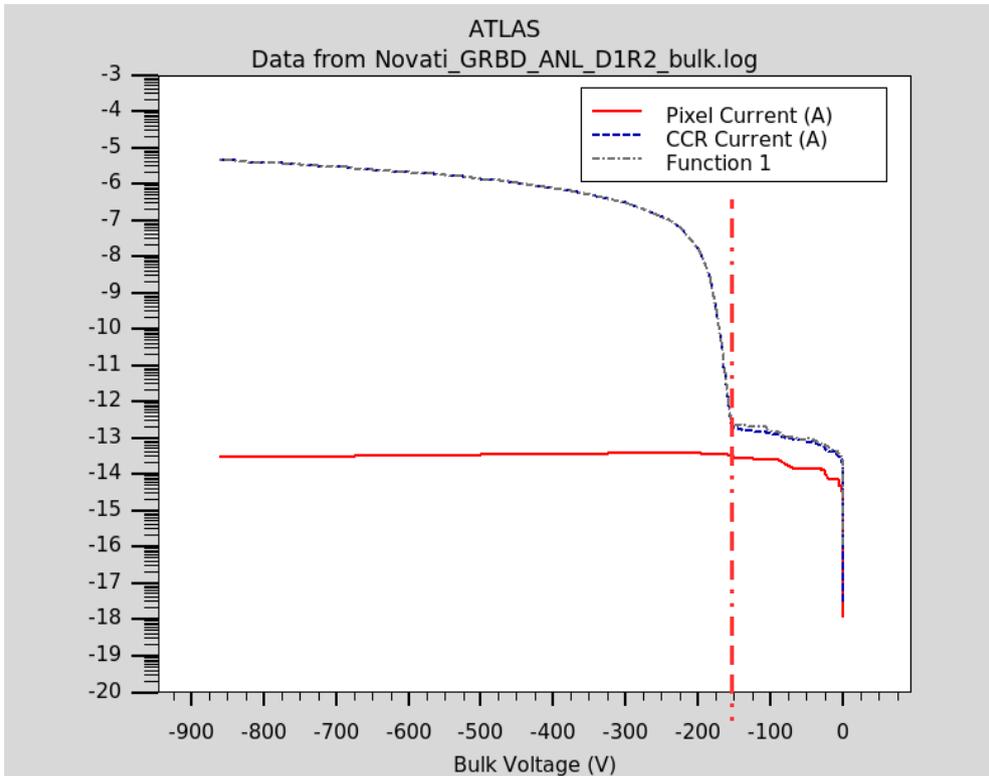
Comparison Summary

Device Type	Breakdown Voltage	Punchthrough
10-um-wide P-stop	-560 V	No
6-um-wide P-stop (shrunk device)	-750 V	No
'Shroom device	-1250 V	Yes 

Conclusions

- Unexpectedly, suppressing vertical electrical field resulted a substantial improvement.
 - Not to mention that the distance from N-implant was extended when we moved p-stop implant: pushed down the breakdown point even further.
- However, we need to actually implement and verify the 'Shroom' design.
- According to Nov. 30th meeting, Novati will reduce p-stop doping concentration which would improve breakdown strength even further.

1st Device with $Q_{ss} = 6.7e12$



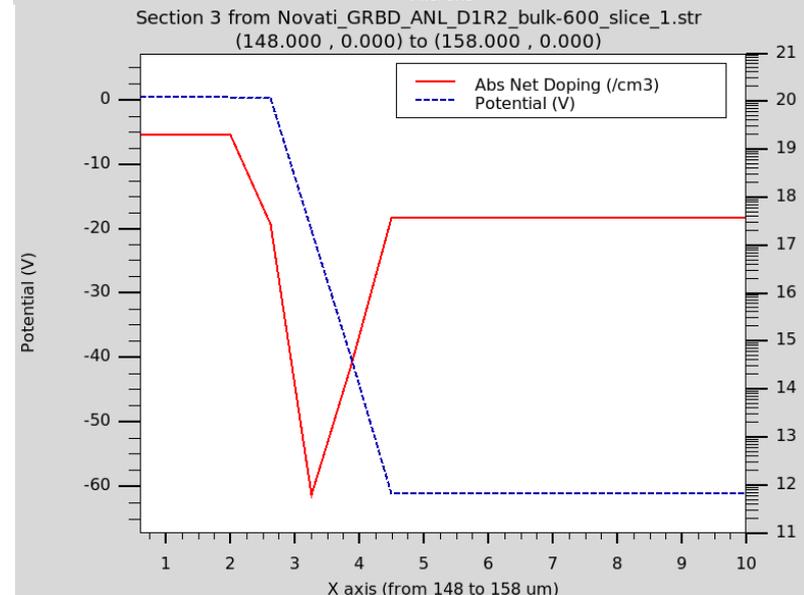
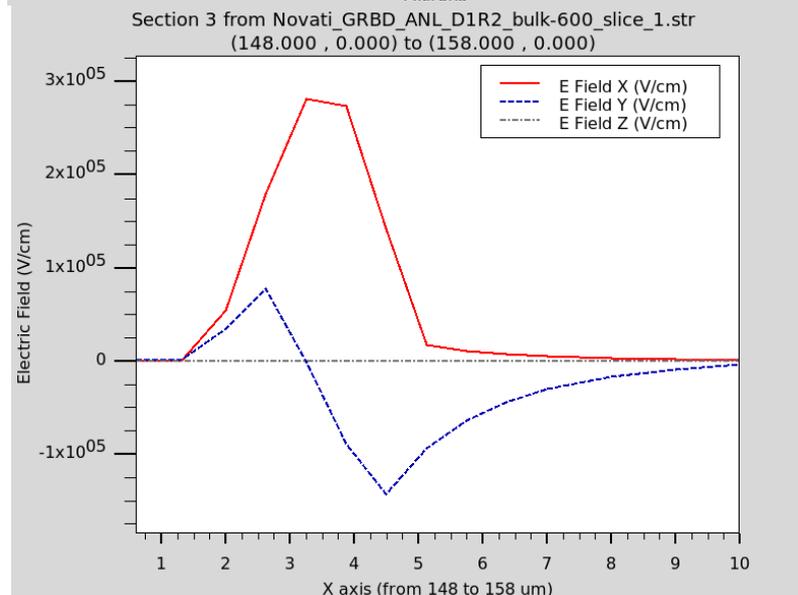
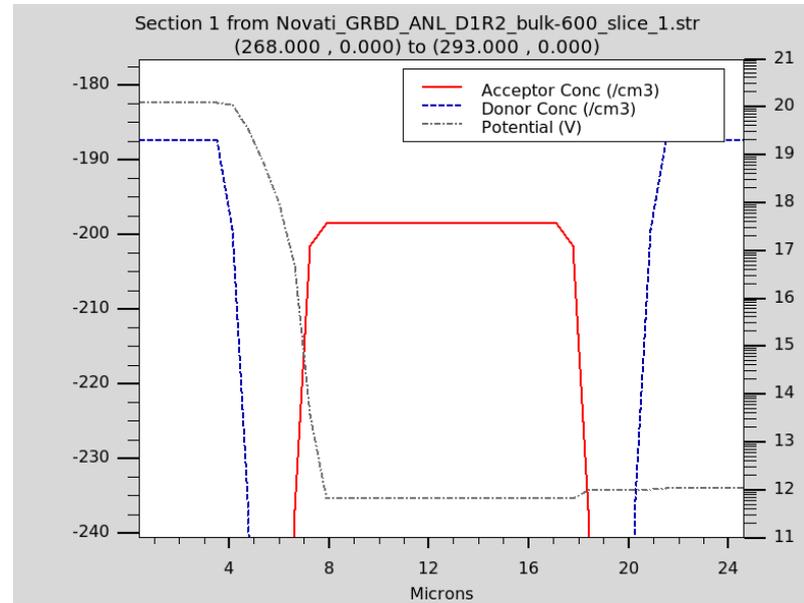
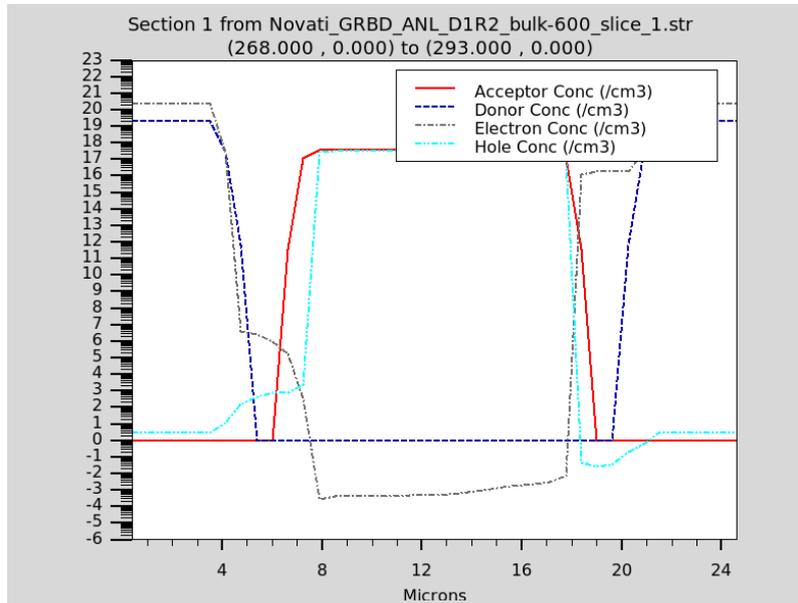
10 μm -wide p-stop device with $Q_{ss} = 6.7e12$

→ Such high Q_{ss} is normally found in polysilicon TFT simulations. (where, oxide is chemically 'deposited')

Breakdown at -150 V

→ Punchthrough was not found but the device is useless to prevent plasma delay effect.

E-field and potential at the 1st GR vicinity



Some more fancy 2D contours

